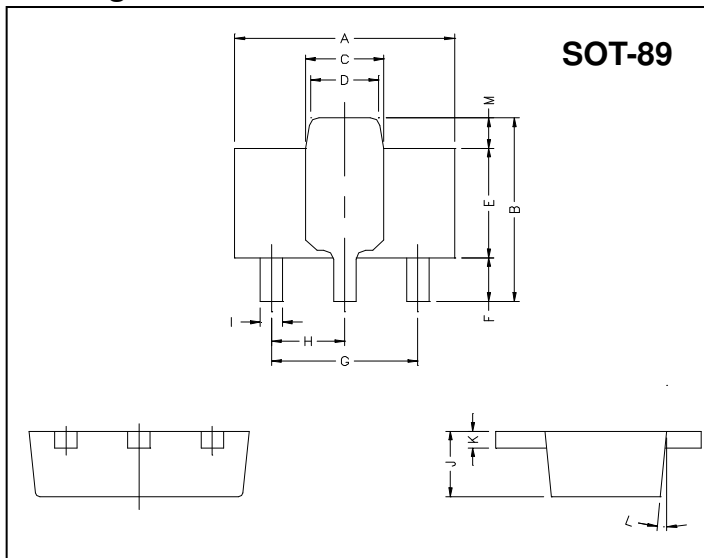
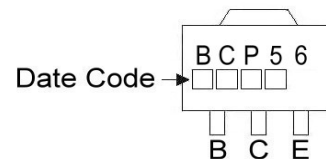


GMBCP56**NPN SILICON EPITAXIAL TRANSISTOR****Description**

The GMBCP56 is designed for use in audio amplifiers and medium power amplifications.

Features

- Collector-Emitter Voltage: $V_{CEO}=80V$
- Complementary to GMBCX53

Package Dimensions**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 ~ +150	$^\circ\text{C}$
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collect Current(DC)	I_C	1	A
Total Power Dissipation	P_D	1.2	W

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

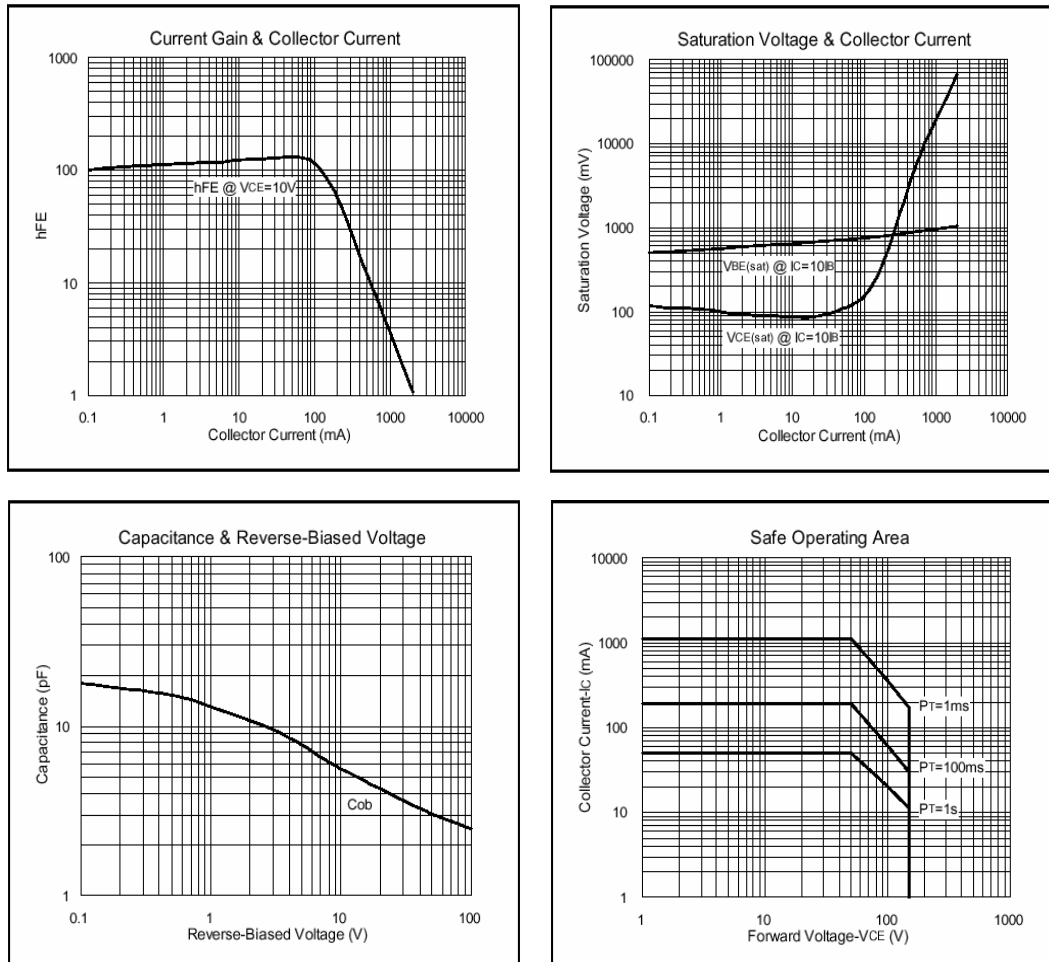
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	100	-	-	V	$I_C=100\mu\text{A}$, $I_E=0$
V_{CEO}	80	-	-	V	$I_C=1\text{mA}$, $I_B=0$
V_{EBO}	5	-	-	V	$I_E=10\mu\text{A}$, $I_C=0$
I_{CBO}	-	-	100	nA	$V_{CB}=30V$, $I_E=0$
I_{EBO}	-	-	100	nA	$V_{EB}=5V$, $I_C=0$
* $V_{CE(sat)1}$	-	-	500	mV	$I_C=500\text{mA}$, $I_B=50\text{mA}$
* $V_{BE(on)}$	-	-	1000	mV	$I_C=500\text{mA}$, $V_{CE}=2V$,
* h_{FE1}	63	-	-		$V_{CE}=2V$, $I_C=5\text{mA}$
* h_{FE2}	63	-	250		$V_{CE}=2V$, $I_C=150\text{mA}$
* h_{FE3}	40	-	-		$V_{CE}=2V$, $I_C=500\text{mA}$
fT	100	-	-	MHz	$V_{CE}=5V$, $I_C=10\text{mA}$

* Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

Classification Of h_{FE2}

Rank	10	16
Range	63 - 160	100 - 250

Characteristics Curve



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